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for a capacitor dielectric layer where both of layers 18 and 20 are crystalline in their final form, an interface line 19 essentially forms therebetween where such discrete layers contact (Fig. 5). Interface line 19 is characterized by a perceptible change in crystallinity from one layer to the other, such as shown or evidenced in this example by a substantial lateral shift or displacement in grain boundaries from one layer to the other.--.

In the Claims

Please replace the claims with the following clean versions of the claims.

Cancel claim 54.

Sub 017
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38. (Amended) A capacitor comprising a pair of capacitor electrodes having capacitor dielectric material therebetween comprising a composite of two immediately juxtaposed and contacting, yet discrete, layers of the same capacitor dielectric material, both of the discrete layers being crystalline, and comprising an interface where the discrete layers contact which is characterized by a perceptible change in crystallinity from one layer to the other, the perceptible change in crystallinity being characterized by a perceptible interface line between the two discrete layers and a perceptible lateral shift in grain boundaries from the one layer to the other.

42. (Unchanged) The capacitor of claim 38 wherein the same capacitor dielectric material comprises a titanate compound.

43. (Unchanged) The capacitor of claim 38 wherein the same capacitor dielectric material comprises Ta₂O₅.

Sub D17
46. (Amended) The capacitor of claim 38 constituting an entire capacitor dielectric region between the pair of capacitor electrodes, the entire capacitor dielectric region consisting essentially of the composite of the two immediately juxtaposed and contacting, yet discrete, layers of the same capacitor dielectric material.

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47. (Amended) The capacitor of claim 42 constituting an entire capacitor dielectric region between the pair of capacitor electrodes, the entire capacitor dielectric region consisting essentially of the composite of the two immediately juxtaposed and contacting, yet discrete, layers of the same capacitor dielectric material.

48. (Amended) The capacitor of claim 43 constituting an entire capacitor dielectric region between the pair of capacitor electrodes, the entire capacitor dielectric region consisting essentially of the composite of the two immediately juxtaposed and contacting, yet discrete, layers of the same capacitor dielectric material.

49. (Unchanged) The capacitor of claim 38 wherein at least one of the electrodes predominately comprises a material selected from the group consisting of TiN_x , WN_x , TaN_x , $PtRh_x$, $PtRu_x$, $PtIr_x$, and mixtures thereof.

Sub D1
50. (Amended) The capacitor of claim 49 constituting an entire capacitor dielectric region between the pair of capacitor electrodes, the entire capacitor dielectric region consisting essentially of the composite of the two immediately juxtaposed and contacting, yet discrete, layers of the same capacitor dielectric material.

51. (Amended) The capacitor of claim 38 wherein one of the two layers has a thickness of from 10% to 90% of a combined thickness of the two layers.

52. (Amended) The capacitor of claim 51 constituting an entire capacitor dielectric region between the pair of capacitor electrodes, the entire capacitor dielectric region consisting essentially of the composite of the two immediately juxtaposed and contacting, yet discrete, layers of the same capacitor dielectric material.

53. (Unchanged) The capacitor of claim 51 wherein at least one of the electrodes predominately comprises a material selected from the group consisting of TiN_x , WN_x , TaN_x , $PtRh_x$, $PtRu_x$, $PtIr_x$, and mixtures thereof.